## BYZ 50A22 ... BYZ50K39



Silicon Press-fit diodes

## Silicon Protectifiers with TVS characteristics High-temperature diodes BYZ 50A22 ... BYZ50K39

Pulse Power Dissipation: 10000 W

Maximum Stand-off voltage: / V

Publish Data

## Features

- High power diodes
- High temperature diodes

## **Mechanical Data**

- Metal press-fit case with plastic cover
- Casting compound has UL classification 94V-0
- Terminals Ni plated
- Mounting position : any
- Weight approx. : 10 g
- Standard packing : Bulk
- BYZ50Axx anode on wire
- BYZ50Kxx cathode on wire

Absolute Maximum Ratings							
Symbol	Conditions	Values	Units W				
P <sub>PPM</sub>	Peak pulse power dissipation $t_p = 1ms T_a = 25 \text{ °C}$	10000					
P <sub>M(AV)</sub>	Steady state power dissipation <sup>2)</sup> , $T_a = °C$		W				
I <sub>FSM</sub>	Peak forward surge current 50Hz half sin wave, $T_A = 25^{\circ} C T_a = {^{\circ}C}$	360	A				
R <sub>thA</sub>	Max. thermal resistance junction to ambient <sup>2)</sup>		K/W				
R <sub>thT</sub>	Max. thermal resistance junction to terminal	0,6	K/W				
T <sub>j</sub>	Operating junction temperature	-50 +225	°C				
Τ <sub>s</sub>	Storage temperature	-50 +225	°C				
V <sub>f</sub>	Max. instant. forw. voltage $I_f = 100 A^{3}$	<1,1 (BYZ 50A(K)22; 26)	V				
		<1,2 (BYZ 50A(K)32; 36; 39)	V				

Characteristics									
Туре	Max stand-off voltage@I <sub>D</sub>		Breakdown voltage@I <sub>T</sub>		Test current I <sub>T</sub>	Max. clamping voltage@I <sub>PPM</sub>			
	V <sub>WM</sub>	I <sub>D</sub>	min.	max.		V <sub>C</sub>	I <sub>PPM</sub>		
	V	μA	V	V	mA	V	А		
BYZ 50A(K)22	16	10	20	25	100	35	100		
BYZ 50A(K)27	20	10	25	29	100	40	100		
BYZ 50A(K)33	26	10	31	35	100	50	80		
BYZ 50A(K)37	30	10	34	40	100	56	80		
BYZ 50A(K)39	32	10	35	43	100	58	60		

